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Vishay Siliconix

N-Channel 40 V (D-S) MOSFET

| View | Bottom Vi |
|------|-----------|
| | |

| PRODUCT SUMMARY | | | | | | |
|--|-----------------|--|--|--|--|--|
| V _{DS} (V) | 40 | | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$ | 0.0076 | | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$ | 0.0092 | | | | | |
| Q _g typ. (nC) | 12.5 | | | | | |
| I _D (A) | 35 ^a | | | | | |
| Configuration | Single | | | | | |

FEATURES

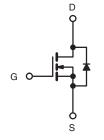
- TrenchFET® power MOSFET
- 100 % R_g and UIS tested





APPLICATIONS

• POL



N-Channel MOSFET

| ORDERING INFORMATION | |
|---------------------------------|------------------|
| Package | PowerPAK 1212-8 |
| Lead (Pb)-free and halogen-free | SiSH434DN-T1-GE3 |

| ABSOLUTE MAXIMUM RATING | iS (T _A = 25 °C, u | ınless other | wise noted) | |
|--|--------------------------------------|-----------------------------------|----------------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V_{DS} | 40 | V |
| Gate-source voltage | | V _{GS} | ± 20 | |
| | T _C = 25 °C | | 35 ^a | |
| Continuous drain augrent (T. 150 °C) | T _C = 70 °C | 1 . | 35 ^a | |
| Continuous drain current (T _J = 150 °C) | T _A = 25 °C | I _D | 17.6 ^{b, c} | _ |
| | T _A = 70 °C | 1 | 14.1 ^{b, c} | A |
| Pulsed drain current Avalanche current | | I _{DM} | 60 | |
| Avalanche current | 1 0.1 ml l | I _{AS} | 30 | |
| Avalanche energy | L = 0.1 mH | E _{AS} | 45 | mJ |
| Continuous source-drain diode current | T _C = 25 °C | | 35 ^a | ^ |
| Continuous source-drain diode current | T _A = 25 °C | - I _S | 3.2 b, c | A |
| | T _C = 25 °C | | 52 | |
| Maximum navvar dissination | T _C = 70 °C | 1 . | 33 | 14/ |
| Maximum power dissipation | T _A = 25 °C | P _D | 3.8 b, c | W |
| | T _A = 70 °C | ĺ | 2 b, c | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +150 | °C |
| Soldering recommendations (peak temperature) d, e | | | 260 | 1 |

| THERMAL RESISTANCE RATI | NGS | | | | | |
|----------------------------------|--------------|------------|---------|---------|------|--|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
| Maximum junction-to-ambient b, f | t ≤ 10 s | R_{thJA} | 24 | 33 | °C/W | |
| Maximum junction-to-case (drain) | Steady state | R_{thJC} | 1.9 | 2.4 | C/VV | |

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 10 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8SH is a leadless package within the PowerPAK 1212-8 package family. The end of the lead terminal is exposedcopper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 81 °C/W



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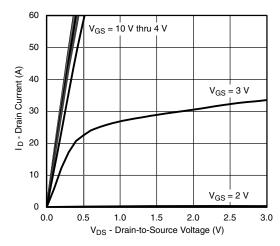
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|--------------------------------------|--|------|--------|--------|-------|
| Static | | | • | | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | 40 | - | - | V |
| V _{DS} temperature coefficient | DV _{DS} /T _J | J 050 · · A | - | 46 | - | >//00 |
| V _{GS(th)} temperature coefficient | DV _{GS(th)} /T _J | I _D = 250 μA | - | -5 | - | mV/°C |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$ | 1.2 | - | 2.2 | V |
| Gate-source leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA |
| 7 | | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$ | - | - | 1 | μA |
| Zero gate voltage drain current | I _{DSS} | $V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$ | - | - | 5 | |
| On-state drain current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 40 | - | - | Α |
| Drain course on state resistance 8 | В | V _{GS} = 10 V, I _D = 16.2 A | _ | 0.0063 | 0.0076 | |
| Drain-source on-state resistance a | R _{DS(on)} | $V_{GS} = 4.5 \text{ V}, I_D = 14.7 \text{ A}$ | - | 0.0077 | 0.0092 | Ω |
| Forward transconductance a | 9 _{fs} | V _{DS} = 15 V, I _D = 16.2 A | - | 60 | - | S |
| Dynamic ^b | | | | | | |
| Input capacitance | C _{iss} | | - | 1530 | - | |
| Output capacitance | C _{oss} | $V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$ | - | 240 | - | pF |
| Reverse transfer capacitance | C _{rss} | | - | 100 | - | 1 |
| <u> </u> | 0 | V _{DS} = 20 V, V _{GS} = 10 V, I _D = 16.2 A | - | 25 | 40 | |
| Total gate charge | Q_g | | - | 12.5 | 19 | |
| Gate-source charge | Q_gs | $V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 16.2 \text{ A}$ | - | 3.9 | - | nC |
| Gate-drain charge | Q _{qd} | | - | 3.9 | - | |
| Gate resistance | R_g | f = 1 MHz | 0.2 | 1.3 | 2.6 | Ω |
| Turn-on delay time | t _{d(on)} | | - | 20 | 30 | |
| Rise time | t _r | $V_{DD} = 20 \text{ V}, R_L = 2 \Omega$ | - | 15 | 25 | |
| Turn-off delay time | t _{d(off)} | $I_D \cong 10$ Å, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω | - | 25 | 40 | |
| Fall time | t _f | | - | 12 | 20 | |
| Turn-on delay time | t _{d(on)} | | - | 10 | 15 | ns |
| Rise time | t _r | V_{DD} = 20 V, R_L = 2 Ω | - | 10 | 15 | |
| Turn-off delay time | t _{d(off)} | $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | - | 25 | 40 | |
| Fall time | t _f | | - | 7 | 15 | |
| Drain-Source Body Diode Characterist | ics | | | | | |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | 43 | |
| Pulse diode forward current ^a | I _{SM} | | - | - | 35 | Α |
| Body diode voltage | V _{SD} | I _S = 10 A, V _{GS} = 0 V | - | 0.8 | 1.2 | ٧ |
| Body diode reverse recovery time | t _{rr} | | - | 30 | 45 | ns |
| Body diode reverse recovery charge | Q _{rr} | I _F = 10 A, di/dt = 100 A/μs, | - | 33 | 50 | nC |
| Reverse recovery fall time | t _a | $T_{\rm J} = 25 ^{\circ}{\rm C}$ | - | 20 | - | |
| Reverse recovery rise time | t _b | | _ | 10 | _ | ns |

Notes

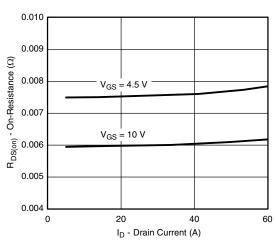
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

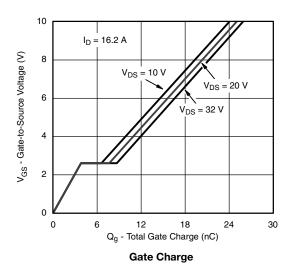


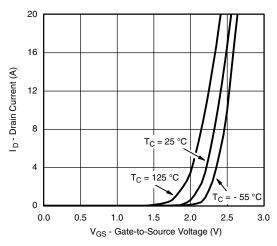


Output Characteristics

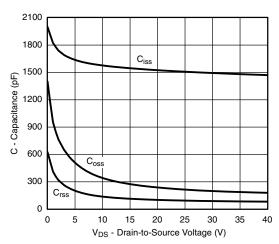


On-Resistance vs. Drain Current and Gate Voltage

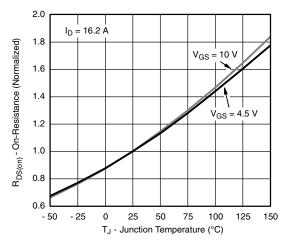




Transfer Characteristics

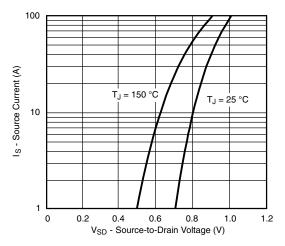


Capacitance

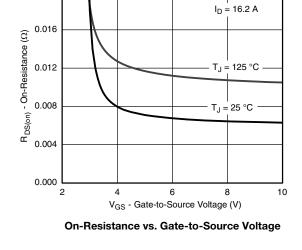


On-Resistance vs. Junction Temperature

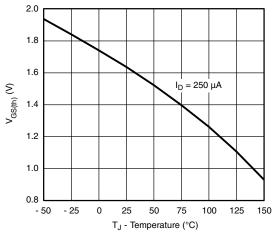




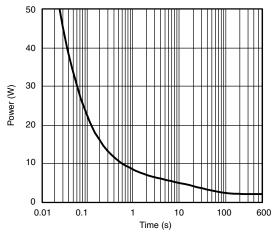
Source-Drain Diode Forward Voltage



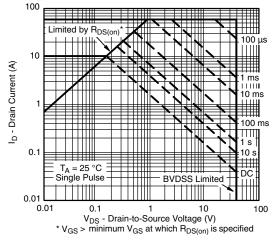
0.020



Threshold Voltage

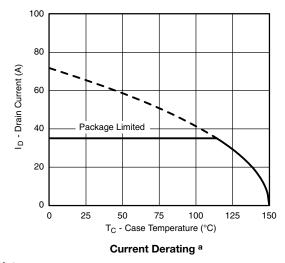


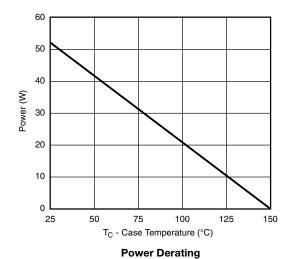
Single Pulse Power (Junction-to-Ambient)



Safe Operating Area, Junction-to-Ambient



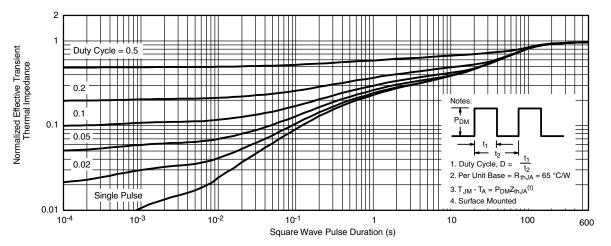




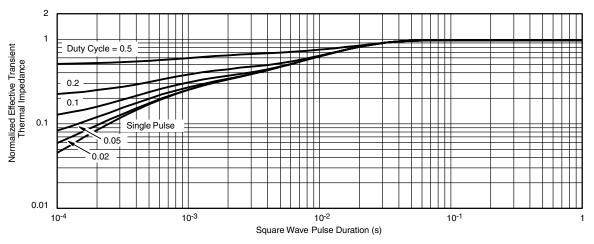
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



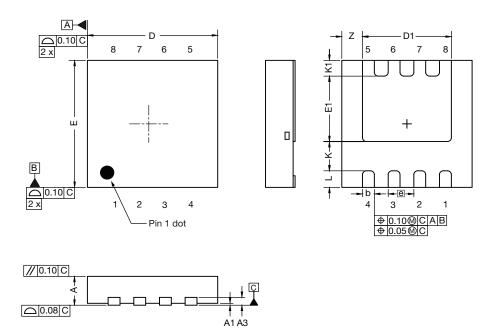
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79242.



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Case Outline for PowerPAK® 1212-SWLH and PowerPAK® 1212-8SH

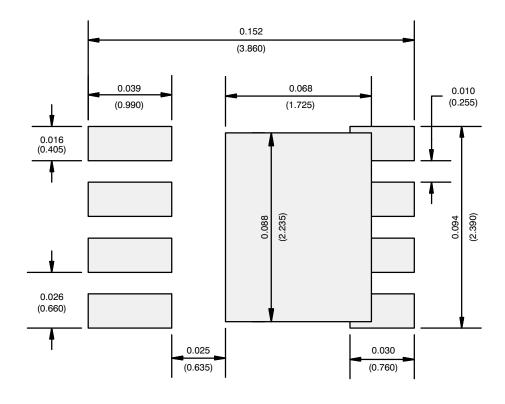


| DIM. | | MILLIMETERS | | | INCHES | | | |
|------|------------|-------------|------------|------------|------------|-------|--|--|
| DIM. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | | |
| Α | 0.82 | 0.90 | 0.98 | 0.032 | 0.035 | 0.038 | | |
| A1 | 0.00 | - | 0.05 | 0.000 | - | 0.002 | | |
| A3 | | 0.20 ref. | | 0.008 ref. | | | | |
| b | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 | | |
| D | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 | | |
| D1 | 2.15 | 2.25 | 2.35 | 0.085 | 0.089 | 0.093 | | |
| Е | 3.20 | 3.30 | 3.40 | 0.126 | 0.130 | 0.134 | | |
| E1 | 1.60 | 1.70 | 1.80 | 0.063 | 0.067 | 0.071 | | |
| е | | 0.65 bsc. | | | 0.026 bsc. | | | |
| K | | 0.76 ref. | | | 0.030 ref. | | | |
| K1 | 0.41 ref. | | 0.016 ref. | | | | | |
| L | 0.33 | 0.43 | 0.53 | 0.013 | 0.017 | 0.021 | | |
| Z | 0.525 ref. | | | 0.021 ref. | | | | |

DWG: 6062



RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



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